

ABSTRACT OF THE DISCLOSURE

Embodiments of the present invention relate to a method for fabricating a Vss line in a memory device, which comprises: forming a plurality of memory cells above a semiconductor substrate, forming a channel between two of the memory cells, forming an oxide/nitride/oxide stack above the memory cells and the channel, removing a portion of the oxide/nitride/oxide stack between the memory cells to expose the semiconductor substrate, removing the oxide/nitride/oxide stack above the gates of the memory cells, forming a plurality of source regions in the substrate between the memory cells, forming a poly-silicon layer above the memory cells and the channel to connect to the source regions, and removing a sufficient portion of the poly-silicon layer to form a Vss line.